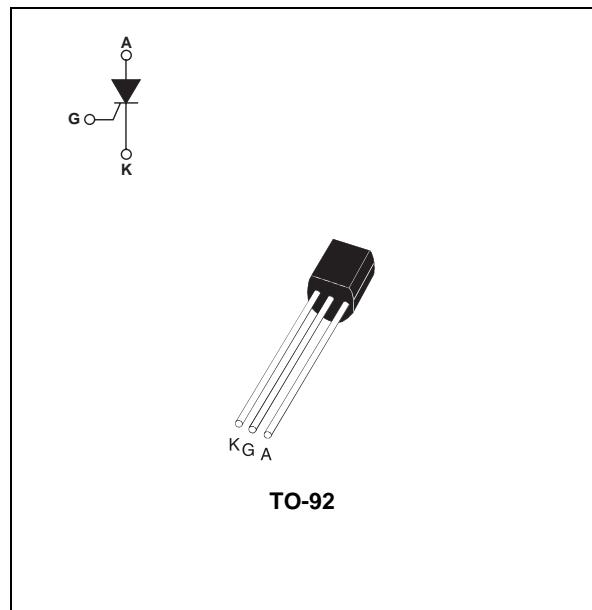


**SENSITIVE**
**0.8A SCRs**
**MAIN FEATURES:**

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
$V_{DRM}/V_{RRM}$	100	V
$I_{GT}$	1	$\mu A$


**DESCRIPTION**

The P0130AA is a gate sensitive SCR, packaged in TO-92, used in conjunction of a TN22 A.S.D.<sup>TM</sup> and of a resistor in electronic starter for fluorescent tubelamps.

**ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)		0.8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)		0.5	A
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	8	A
		$t_p = 10 \text{ ms}$		
$I^2t$	$I^2t$ Value for fusing	$t_p = 10\text{ms}$	$T_j = 25^\circ\text{C}$	$0.24 \text{ A}^2\text{s}$
$dl/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^\circ\text{C}$	$A/\mu\text{s}$
$I_{GM}$	Peak gate current	$t_p = 20 \mu\text{s}$	$T_j = 125^\circ\text{C}$	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	W
$T_{stg}$ $T_j$	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125	$^\circ\text{C}$

## P0130AA

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified)**

Symbol	Test Conditions		P0130AA		Unit	
I <sub>GT</sub>	V <sub>D</sub> = 12 V      R <sub>L</sub> = 140 Ω	MIN.	0.1	μA		
V <sub>GT</sub>		MAX.	1			
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ    R <sub>GK</sub> = 1 kΩ		T <sub>j</sub> = 125°C	MIN.	0.8	V
V <sub>RG</sub>	I <sub>RG</sub> = 10 μA			MIN.	0.1	V
I <sub>H</sub>	I <sub>T</sub> = 50 mA    R <sub>GK</sub> = 1 kΩ			MAX.	5	mA
I <sub>L</sub>	I <sub>G</sub> = 1 mA    R <sub>GK</sub> = 1 kΩ			MAX.	6	mA
dV/dt	V <sub>D</sub> = 67 % V <sub>DRM</sub> R <sub>GK</sub> = 1 kΩ	T <sub>j</sub> = 125°C	MIN.	25	V/μs	
V <sub>TM</sub>	I <sub>TM</sub> = 1.6 A    t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25°C	MAX.	1.95	V	
V <sub>t0</sub>	Threshold voltage	T <sub>j</sub> = 125°C	MAX.	0.95	V	
R <sub>d</sub>	Dynamic resistance	T <sub>j</sub> = 125°C	MAX.	600	mΩ	
I <sub>DRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub> R <sub>GK</sub> = 1 kΩ	T <sub>j</sub> = 25°C	MAX.	1	μA	
I <sub>RRM</sub>		T <sub>j</sub> = 125°C	MAX.	100		

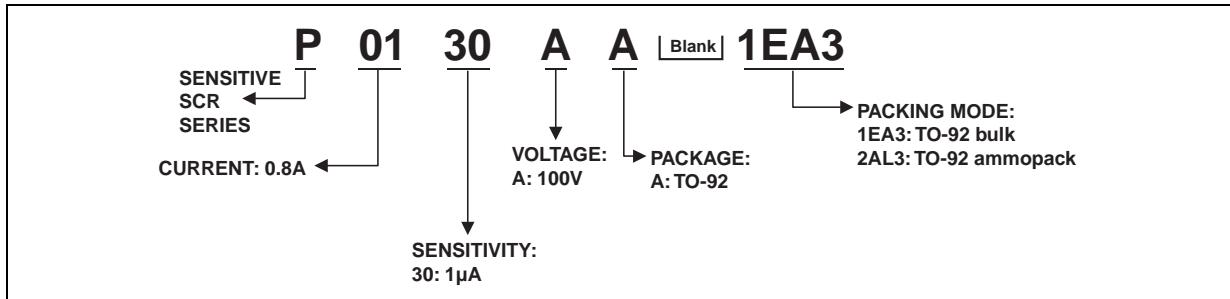
## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-i)</sub>	Junction to case (DC)	80	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	150	°C/W

## PRODUCT SELECTOR

Part Number	Voltage	Sensitivity	Package
P0130AA	100V	1 μA	TO-92

## ORDERING INFORMATION

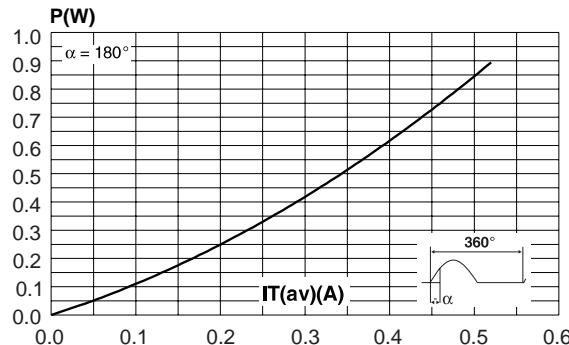


## OTHER INFORMATION

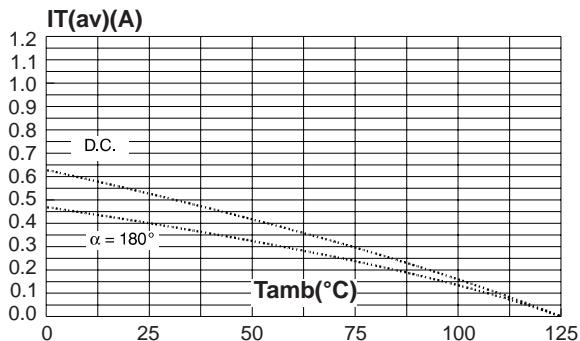
Part Number	Marking	Weight	Base Quantity	Packing mode
P0130AA 1EA3	P0130AA	0.2 g	2500	Bulk
P0130AA 2AL3	P0130AA	0.2 g	2000	Ammopack

Note: xx = sensitivity, y = voltage

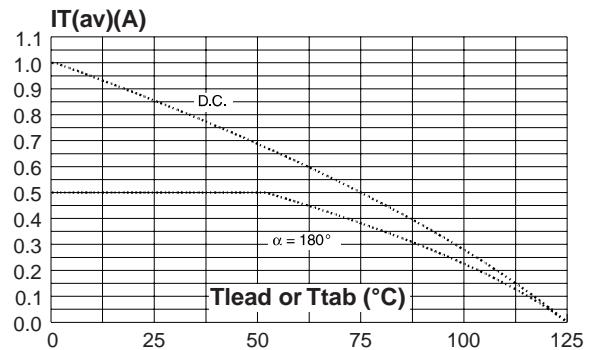
**Fig. 1:** Maximum average power dissipation versus average on-state current.



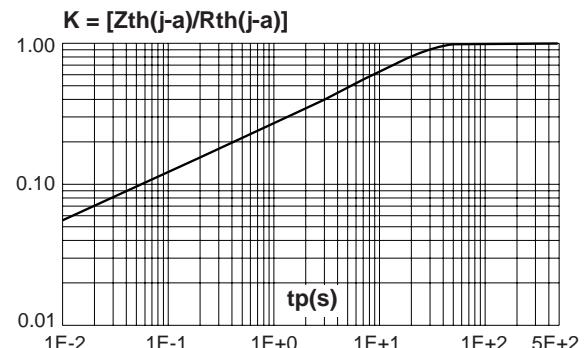
**Fig. 2-2:** Average and D.C. on-state current versus ambient temperature.



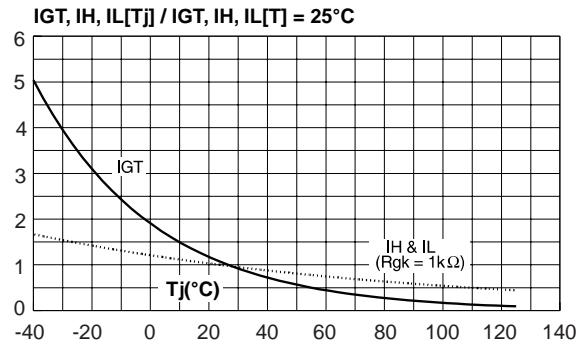
**Fig. 2-1:** Average and D.C. on-state current versus lead temperature.



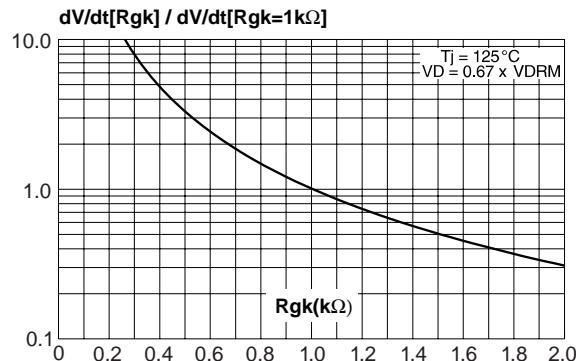
**Fig. 3:** Relative variation of thermal impedance junction to ambient versus pulse duration.



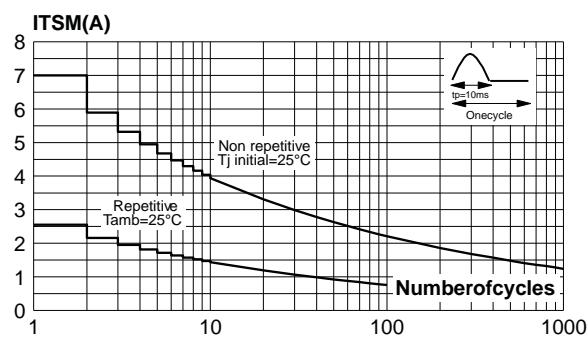
**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



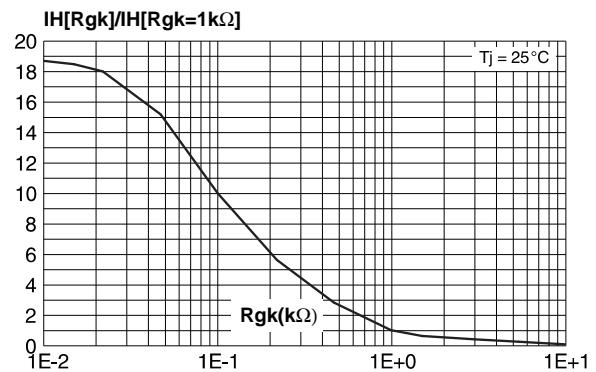
**Fig. 6:** Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).



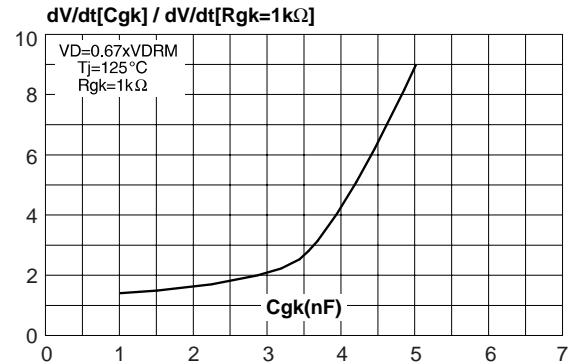
**Fig. 8:** Surge peak on-state current versus number of cycles.



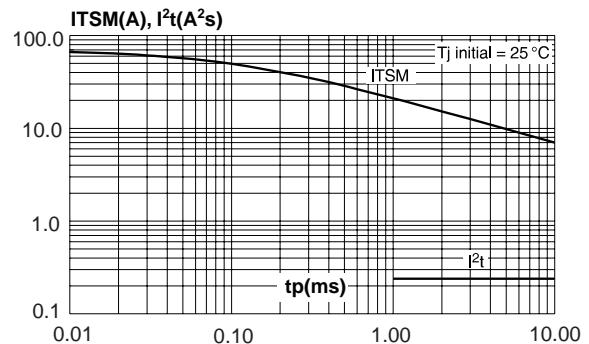
**Fig. 5:** Relative variation of holding current versus gate-cathode resistance (typical values).



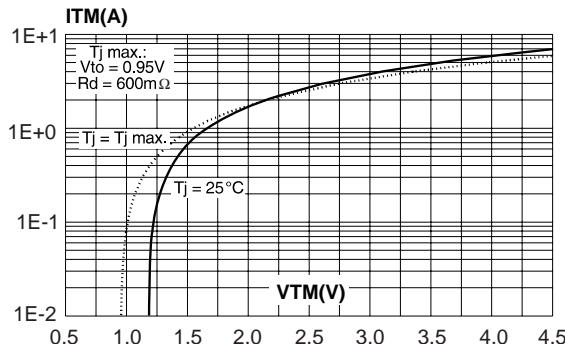
**Fig. 7:** Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values).



**Fig. 9:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms, and corresponding value of I<sup>2</sup>t.



**Fig. 10:** On-state characteristics (maximum values).



## PACKAGE MECHANICAL DATA

TO-92 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.053	
B			4.70			0.185
C		2.54			0.100	
D	4.40			0.173		
E	12.70			0.500		
F			3.70			0.146
a			0.50			0.019

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